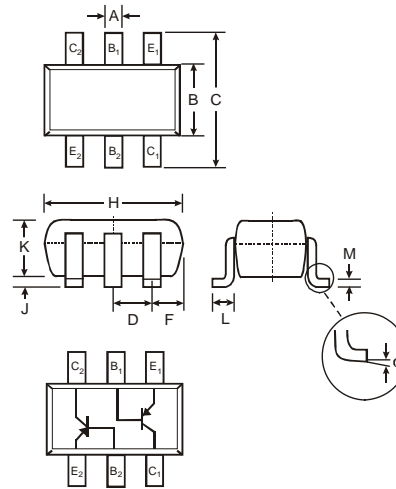


### Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**

### Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering and Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
$\alpha$	0°	8°

All Dimensions in mm

### Maximum Ratings @<sub>T<sub>A</sub></sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous (Note 1)	$I_C$	-600	mA
Total Power Dissipation (Note 1)	$P_d$	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	$T_i, T_{STG}$	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead.

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 3)</b>					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-60	—	V	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-60	—	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CBO</sub>	—	-10	nA μA	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0 V <sub>CB</sub> = -50V, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C
Collector Cutoff Current	I <sub>CES</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -0.5V
Base Cutoff Current	I <sub>BL</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -0.5V
<b>ON CHARACTERISTICS (Note 3)</b>					
DC Current Gain	h <sub>FE</sub>	75 100 100 100 50	— — — 300 —	—	I <sub>C</sub> = -100μA, V <sub>CE</sub> = -10V I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -10V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V I <sub>C</sub> = -150mA, V <sub>CE</sub> = -10V I <sub>C</sub> = -500mA, V <sub>CE</sub> = -10V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-0.4 -1.6	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	-1.3 -2.6	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	8.0	pF	V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	30	pF	V <sub>EB</sub> = -2.0V, f = 1.0MHz, I <sub>C</sub> = 0
Current Gain-Bandwidth Product	f <sub>T</sub>	200	—	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -50mA, f = 100MHz
<b>SWITCHING CHARACTERISTICS</b>					
Turn-On Time	t <sub>off</sub>	—	45	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA, I <sub>B1</sub> = -15mA
Delay Time	t <sub>d</sub>	—	10	ns	
Rise Time	t <sub>r</sub>	—	40	ns	
Turn-Off Time	t <sub>off</sub>	—	100	ns	V <sub>CC</sub> = -6.0V, I <sub>C</sub> = -150mA, I <sub>B1</sub> = I <sub>B2</sub> = -15mA
Storage Time	t <sub>s</sub>	—	80	ns	
Fall Time	t <sub>f</sub>	—	30	ns	

Notes: 3. Short duration pulse test used to minimize self-heating effect.

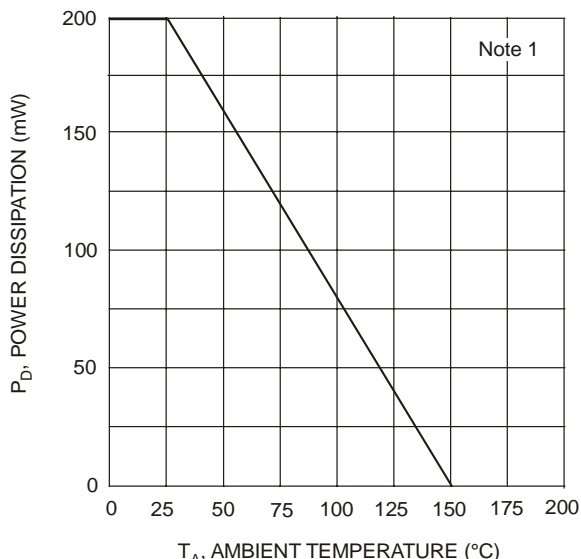


Fig. 1, Max Power Dissipation vs Ambient Temperature (Total Device)

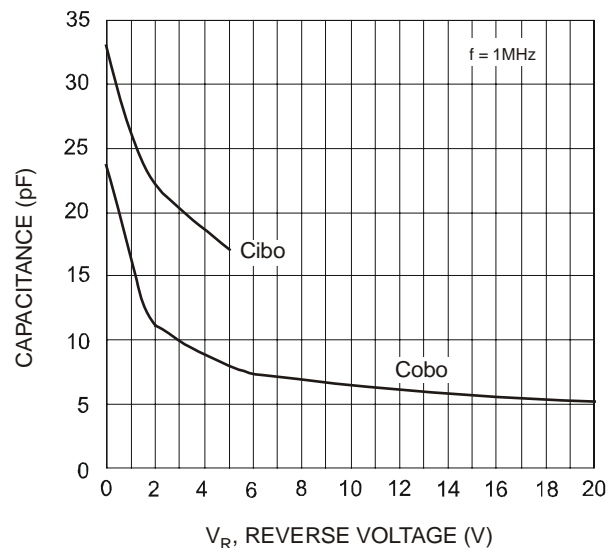


Fig. 2, Typical Capacitance Characteristics

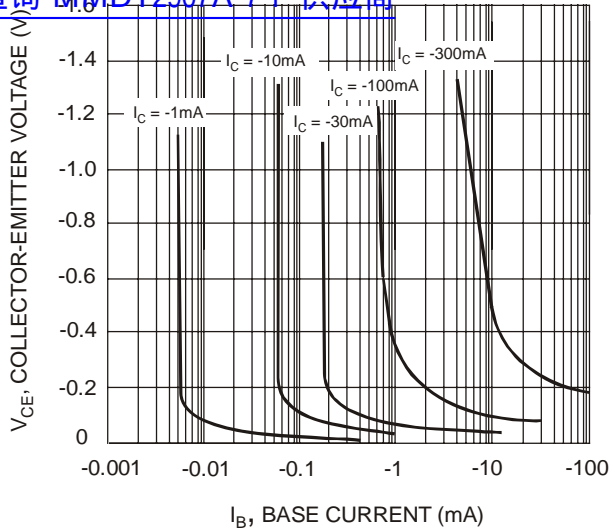


Fig. 3, Typical Collector Saturation Region

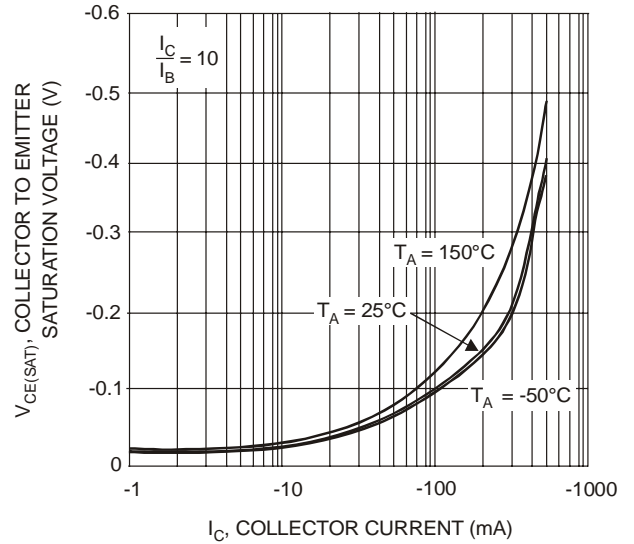


Fig. 4, Collector Emitter Saturation Voltage vs. Collector Current

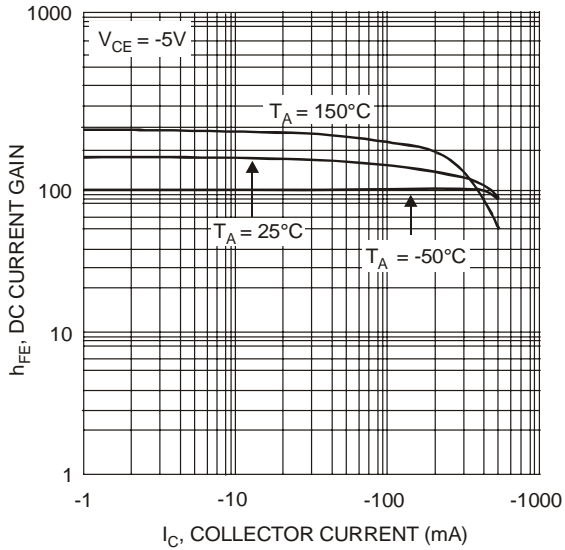


Fig. 5, DC Current Gain vs. Collector Current

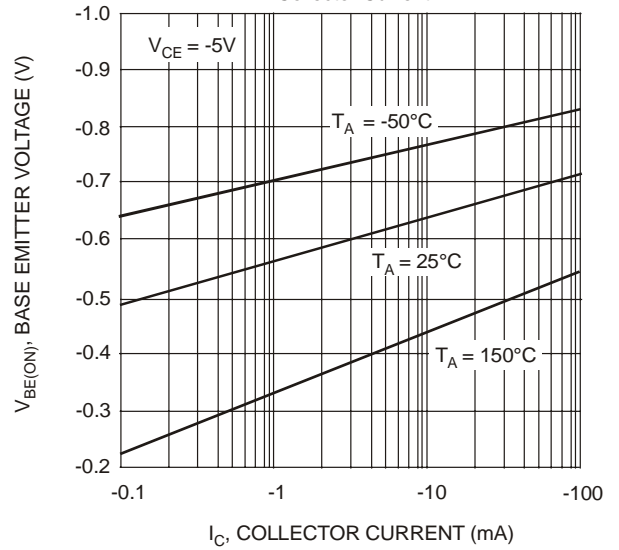


Fig. 6, Base Emitter Voltage vs. Collector Current

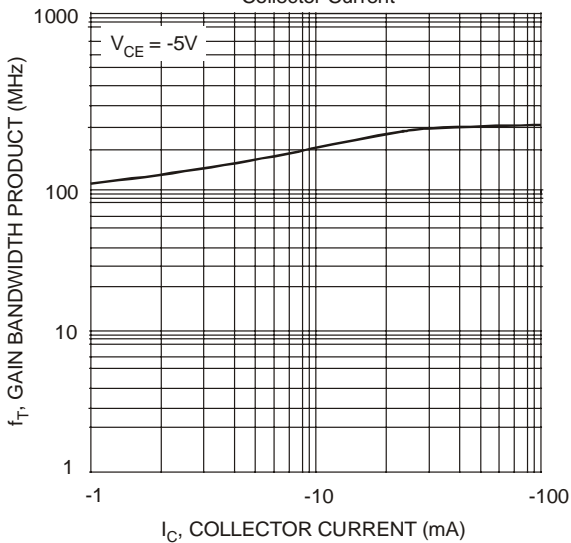


Fig. 7, Gain Bandwidth Product vs. Collector Current

Device	Packaging	Shipping
MMDT2907A-7-F	SOT-363	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



K2F = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

### Data Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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